



FZT957

#### 300V PNP MEDIUM POWER TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > -300V
- I<sub>C</sub> = -1A High Continuous Collector Current
- I<sub>CM</sub> = -2A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -240mV @ -1A</li>
- h<sub>FE</sub> Specified up to -2A for a High Gain Hold-Up
- Complementary NPN Type: FZT857
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

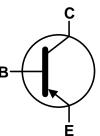
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.112 grams (Approximate)

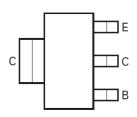




Top View



Device Symbol



Top View Pin-Out

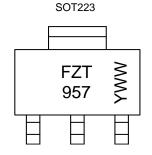
#### Ordering Information (Notes 4 & 5)

| Product   | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-----------|------------|---------|--------------------|-----------------|-------------------|
| FZT957TA  | AEC-Q101   | FZT957  | 7                  | 12              | 1,000             |
| FZT957TC  | AEC-Q101   | FZT957  | 13                 | 12              | 4,000             |
| FZT957QTC | Automotive | FZT957  | 13                 | 12              | 4,000             |

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



FZT 957 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 6= 2016) WW or  $\overline{W}W$  = Week Code (01~53)

FZT957 1 of 7
Datasheet Number: DS33191 Rev. 7 - 2 Downloaded From Oneyac.com



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic               | Symbol    | Value | Unit |
|------------------------------|-----------|-------|------|
| Collector-Base Voltage       | $V_{CBO}$ | -330  | V    |
| Collector-Emitter Voltage    | $V_{CEO}$ | -300  | V    |
| Emitter-Base Voltage         | $V_{EBO}$ | -7    | V    |
| Continuous Collector Current | Ic        | -1    | Α    |
| Peak Pulse Current           | Ісм       | -2    | Α    |

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                            | Symbol           | Value           | Unit        |        |  |
|---|------------------|-----------------|-------------|--------|--|
| Power Dissipation                         | (Note 6)         |                 | 3<br>24     | W      |  |
| Linear Derating Factor                    | (Note 7)         | P <sub>D</sub>  | 1.6<br>12.8 | mW /°C |  |
| Thermal Desistance Junction to Ambient    | (Note 6)         | $R_{\theta JA}$ | 42          |        |  |
| Thermal Resistance, Junction to Ambient   | (Note 7)         | $R_{\theta JA}$ | 78          | °C/W   |  |
| Thermal Resistance Junction to Lead (Note |                  | $R_{	heta JL}$  | 8.8         |        |  |
| Operating and Storage Temperature Range   | $T_{J_i}T_{STG}$ | -55 to +150     | °C          |        |  |

# ESD Ratings (Note 9)

| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 8,000 | ٧    | 3B          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | С           |

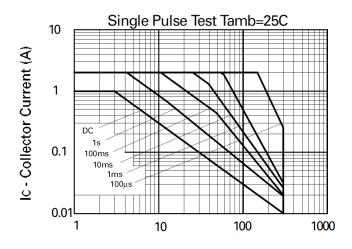
Notes:

- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

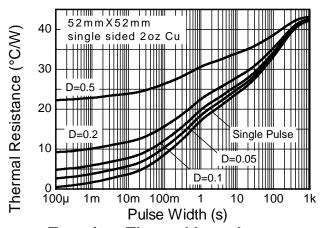


# **Thermal Characteristics and Derating Information**

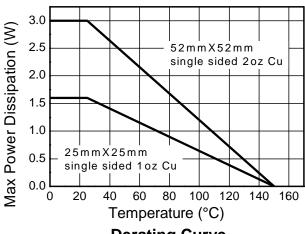




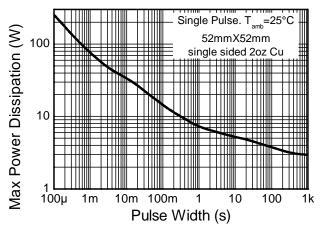
### Safe Operating Area



**Transient Thermal Impedance** 



**Derating Curve** 



**Pulse Power Dissipation** 



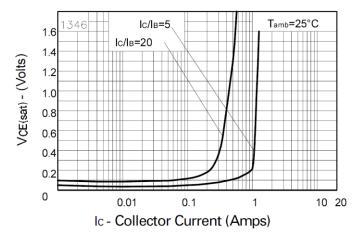
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

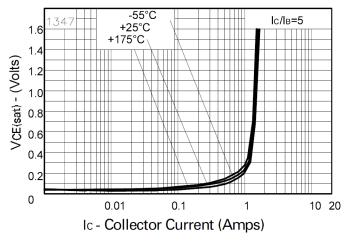
| Characteristic                                 | Symbol               | Min  | Тур   | Max    | Unit | Test Condition   |
|--|----------------------|------|-------|--------|------|--|
| Collector-Base Breakdown Voltage               | BV <sub>CBO</sub>    | -330 | -440  | _      | V    | I <sub>C</sub> = -100μA                                      |
| Collector-Emitter Breakdown Voltage            | BV <sub>CER</sub>    | -330 | -440  | _      | V    | $I_C = -1\mu A, R_B \le 1k\Omega$                            |
| Collector-Emitter Breakdown Voltage (Note 10)  | BV <sub>CEO</sub>    | -300 | -400  | _      | V    | I <sub>C</sub> = -10mA                                       |
| Emitter-Base Breakdown Voltage                 | BV <sub>EBO</sub>    | -7   | -8    | _      | V    | I <sub>E</sub> = -100μA                                      |
| Collector Cut-Off Current                      | lana                 | _    | <1    | -50    | nA   | V <sub>CB</sub> = -300V; R ≤1kΩ                              |
| Collector Cut-Oil Current                      | I <sub>CBO</sub>     | _    | _     | -1     | μΑ   | $V_{CB} = -300V, T_A = +100^{\circ}C$                        |
| Collector Cut-Off Current                      | ICER                 | _    | <1    | -50    | nA   | V <sub>CE</sub> = -300V                                      |
| Conector Gut-On Gurrent                        | ICER                 | _    | _     | -1     | μA   | $V_{CE} = -300V, T_A = +100^{\circ}C$                        |
| Emitter Cut-Off Current                        | I <sub>EBO</sub>     | _    | <1    | -10    | nA   | $V_{EB} = -6V$   |
|  | h <sub>FE</sub>      | 100  | 200   | -      |      | $I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$                 |
| DC Current Transfer Static Patie (Note 10)     |                      | 100  | 200   | 300    | _    | $I_C = -0.5A$ , $V_{CE} = -10V$                              |
| DC Current Transfer Static Ratio (Note 10)     |                      | 90   | 170   | _      |      | I <sub>C</sub> = -1A, V <sub>CE</sub> = -10V                 |
|  |                      | _    | 10    | _      |      | I <sub>C</sub> = -2A, V <sub>CE</sub> = -10V                 |
|  | V <sub>CE(sat)</sub> | _    | -60   | -100   |      | I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA              |
| Collector-Emitter Saturation Voltage (Note 10) |                      | _    | -110  | -165   | mV   | $I_C = -500 \text{mA}, I_B = -100 \text{mA}$                 |
|  |                      | _    | -170  | -240   |      | I <sub>C</sub> = -1A, I <sub>B</sub> = -300mA                |
| Base-Emitter Saturation Voltage (Note 10)      | V <sub>BE(sat)</sub> | _    | -910  | -1,150 | mV   | I <sub>C</sub> = -1A, I <sub>B</sub> = -300mA                |
| Base-Emitter Turn-on Voltage (Note 10)         | V <sub>BE(on)</sub>  | _    | -750  | -1,020 | mV   | I <sub>C</sub> = -1A, V <sub>CE</sub> = -10V                 |
| Transitional Frequency                         | f <sub>T</sub>       |      | 85    |        | MHz  | $I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$<br>f = 50 MHz |
| Output Capacitance                             | C <sub>obo</sub>     | _    | 23    | _      | pF   | V <sub>CB</sub> = -20V, f = 1MHz                             |
| Cuitching Time                                 | t <sub>ON</sub>      | _    | 108   | _      |      | V <sub>CC</sub> = -100V, I <sub>C</sub> = -500mA,            |
| Switching Time                                 | t <sub>OFF</sub>     | _    | 2,500 | _      | ns   | $-I_{B1} = I_{B2} = -50 \text{mA}$                           |

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



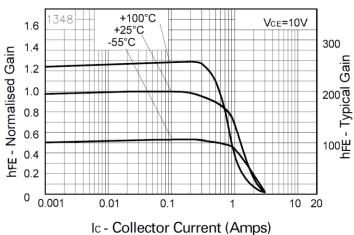
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

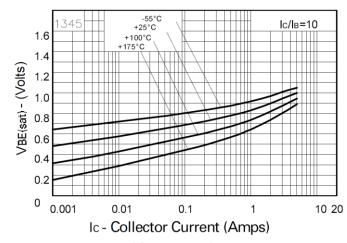




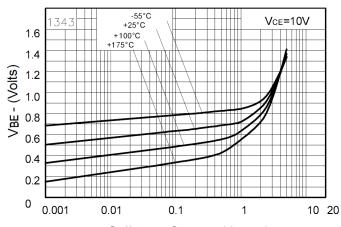
#### VCE(sat) v IC







VBE(sat) v IC



hfe v IC

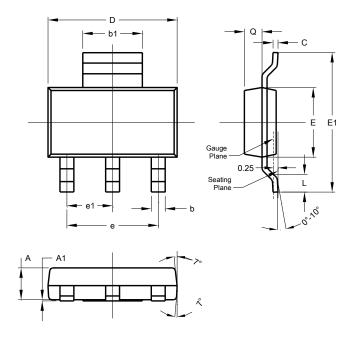
Ic - Collector Current (Amps)

VBE(on) v IC



# **Package Outline Dimensions**

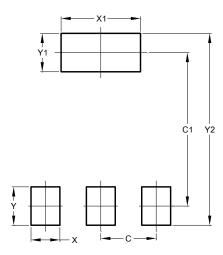
Please see http://www.diodes.com/package-outlines.html for the latest version.



| SOT223               |       |      |      |  |  |
|----------------------|-------|------|------|--|--|
| Dim                  | Min   | Max  | Тур  |  |  |
| Α                    | 1.55  | 1.65 | 1.60 |  |  |
| A1                   | 0.010 | 0.15 | 0.05 |  |  |
| b                    | 0.60  | 0.80 | 0.70 |  |  |
| b1                   | 2.90  | 3.10 | 3.00 |  |  |
| С                    | 0.20  | 0.30 | 0.25 |  |  |
| D                    | 6.45  | 6.55 | 6.50 |  |  |
| Е                    | 3.45  | 3.55 | 3.50 |  |  |
| E1                   | 6.90  | 7.10 | 7.00 |  |  |
| е                    | -     | -    | 4.60 |  |  |
| e1                   | -     | -    | 2.30 |  |  |
| L                    | 0.85  | 1.05 | 0.95 |  |  |
| Q                    | 0.84  | 0.94 | 0.89 |  |  |
| All Dimensions in mm |       |      |      |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.30          |
| C1         | 6.40          |
| Х          | 1.20          |
| X1         | 3.30          |
| Y          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8.00          |



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